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ABSTRACT OF THE DISCLOSURE

Various circuit devices incorporating junction-traversing dislocation regions and methods of making the same are provided. In one aspect, a method of processing is provided that includes forming an impurity region in a device region of a semiconductor-on-insulator substrate. The impurity region defines a junction. A dislocation region is formed in the device region that traverses the junction. The dislocation region provides a pathway to neutralize charge lingering in a floating body of a device.